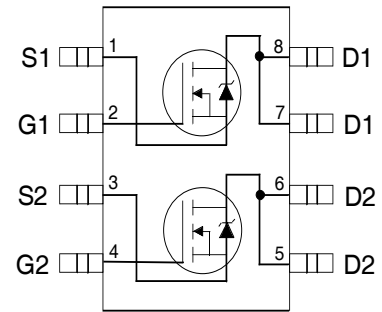


Application

- Generation V Technology
- Ultra Low On-Resistance
- Dual N-Channel Mosfet
- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Fast Switching
- Lead-Free

Features

- $V_{DS} (V) = 20V$
- $R_{DS(ON)} < 50m\Omega$ ($V_{GS} = 4.5V$)
- $R_{DS(ON)} < 70m\Omega$ ($V_{GS} = 2.7V$)



Top View

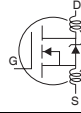
Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ C$	10 Sec. Pulsed Drain Current, $V_{GS} @ 4.5V$	5.7	A
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	5.2	
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	4.1	
I_{DM}	Pulsed Drain Current ①	21	
$P_D @ T_A = 25^\circ C$	Power Dissipation	2.0	W
	Linear Derating Factor	0.016	W/°C
V_{GS}	Gate-to-Source Voltage	± 12	V
dv/dt	Peak Diode Recovery dv/dt ②	5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

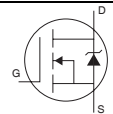
Thermal Resistance Ratings

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	---	62.5	°C/W

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.044	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	—	—	50	mΩ	$V_{GS} = 4.5V, I_D = 2.6A$ ③
		—	—	70		$V_{GS} = 2.7V, I_D = 2.2A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	0.70	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	8.3	—	—	S	$V_{DS} = 15V, I_D = 2.6A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 16V, V_{GS} = 0V$
		—	—	25		$V_{DS} = 16V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 12V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -12V$
Q_g	Total Gate Charge	—	—	20	nC	$I_D = 2.6A$
Q_{gs}	Gate-to-Source Charge	—	—	2.2		$V_{DS} = 16V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	8.0		$V_{GS} = 4.5V$, See Fig. 6 and 12 ③
$t_{d(on)}$	Turn-On Delay Time	—	9.0	—	ns	$V_{DD} = 10V$ $I_D = 2.6A$ $R_G = 6.0\Omega$ $R_D = 3.8\Omega$, See Fig. 10 ③
t_r	Rise Time	—	42	—		
$t_{d(off)}$	Turn-Off Delay Time	—	32	—		
t_f	Fall Time	—	51	—		
L_D	Internal Drain Inductance	—	4.0	—	nH	Between lead tip and center of die contact 
L_S	Internal Source Inductance	—	6.0	—		
C_{iss}	Input Capacitance	—	660	—	pF	$V_{GS} = 0V$ $V_{DS} = 15V$ $f = 1.0MHz$, See Fig. 5
C_{oss}	Output Capacitance	—	280	—		
C_{riss}	Reverse Transfer Capacitance	—	140	—		

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	21		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 1.8A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	29	44	ns	$T_J = 25^\circ\text{C}, I_F = 2.6A$
Q_{rr}	Reverse Recovery Charge	—	22	33	nC	$di/dt = 100A/\mu s$ ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② $I_{SD} \leq 2.6A, di/dt \leq 100A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$
- ③ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ④ Surface mounted on FR-4 board, $t \leq 10sec$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

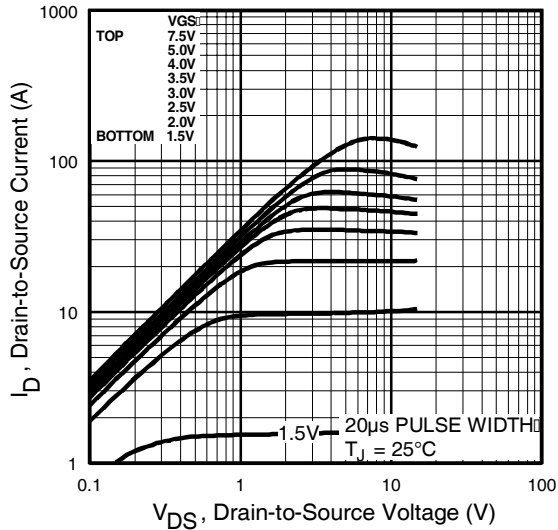


Fig 1. Typical Output Characteristics

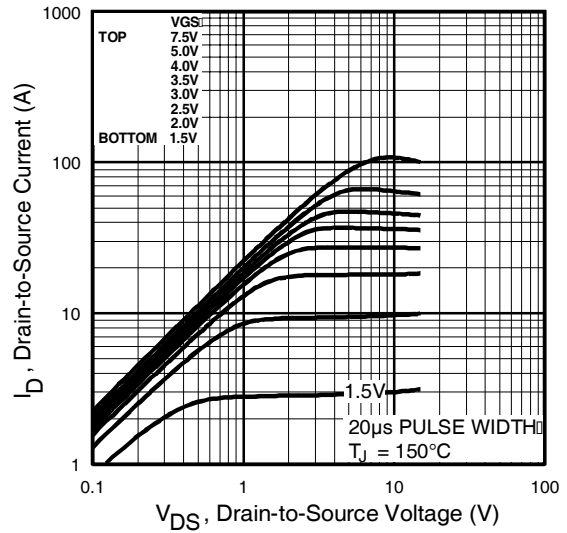


Fig 2. Typical Output Characteristics

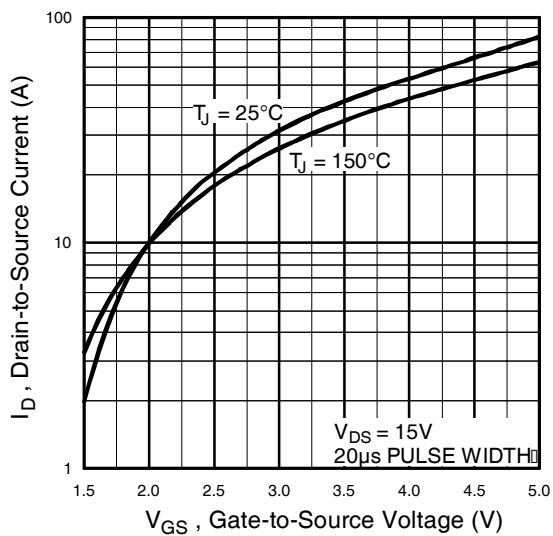


Fig 3. Typical Transfer Characteristics

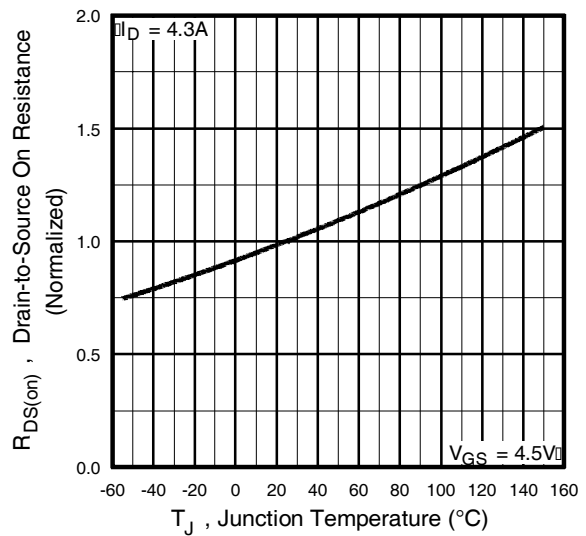


Fig 4. Normalized On-Resistance Vs. Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

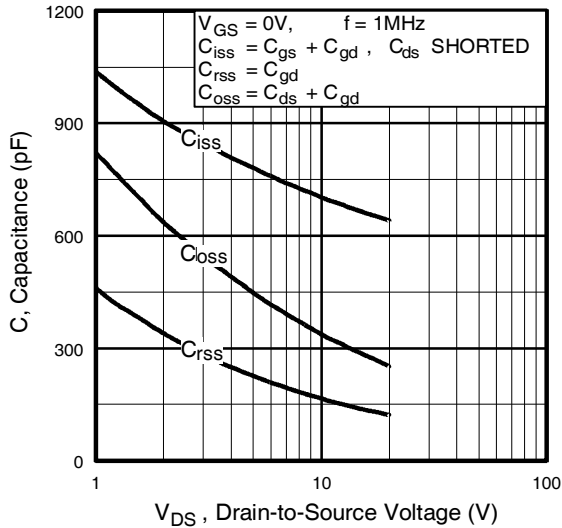


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

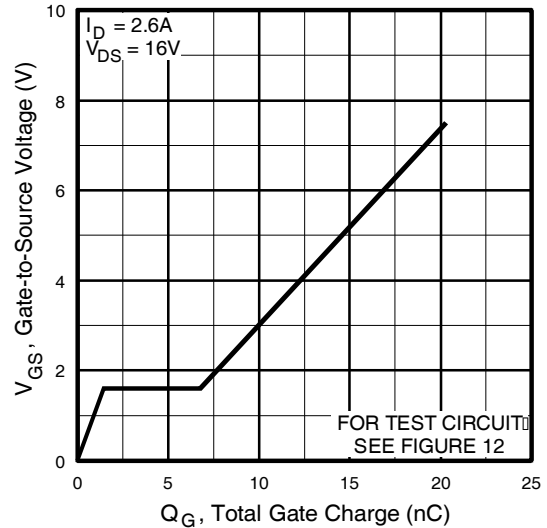


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

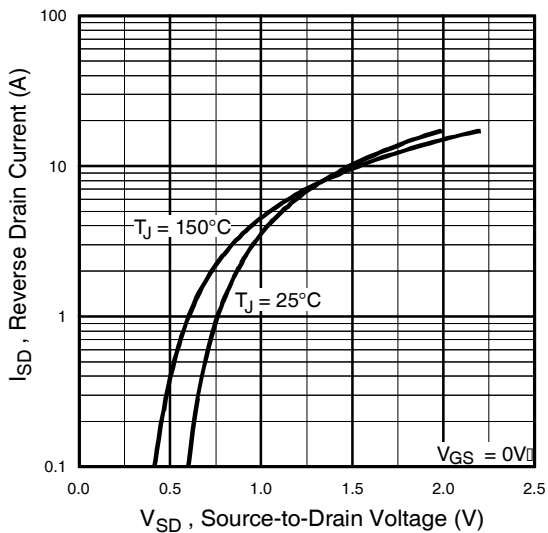


Fig 7. Typical Source-Drain Diode Forward Voltage

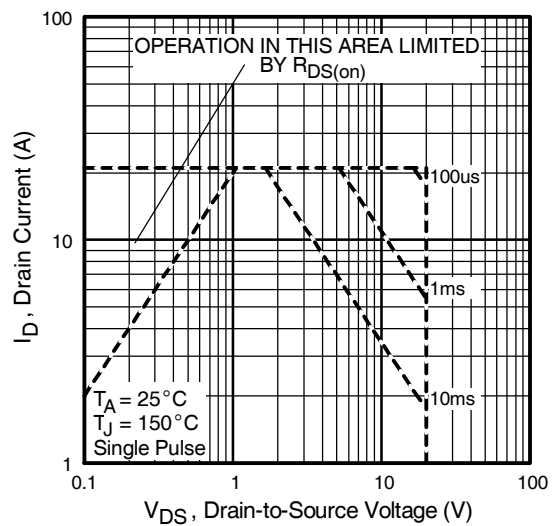


Fig 8. Maximum Safe Operating Area

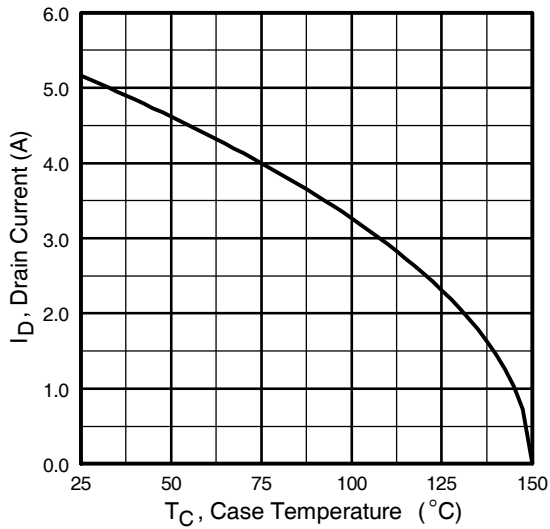


Fig 9. Maximum Drain Current Vs. Ambient Temperature

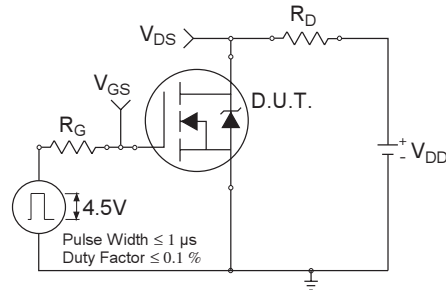


Fig 10a. Switching Time Test Circuit

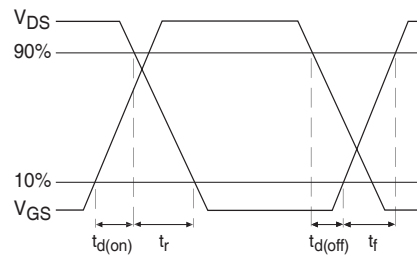


Fig 10b. Switching Time Waveforms

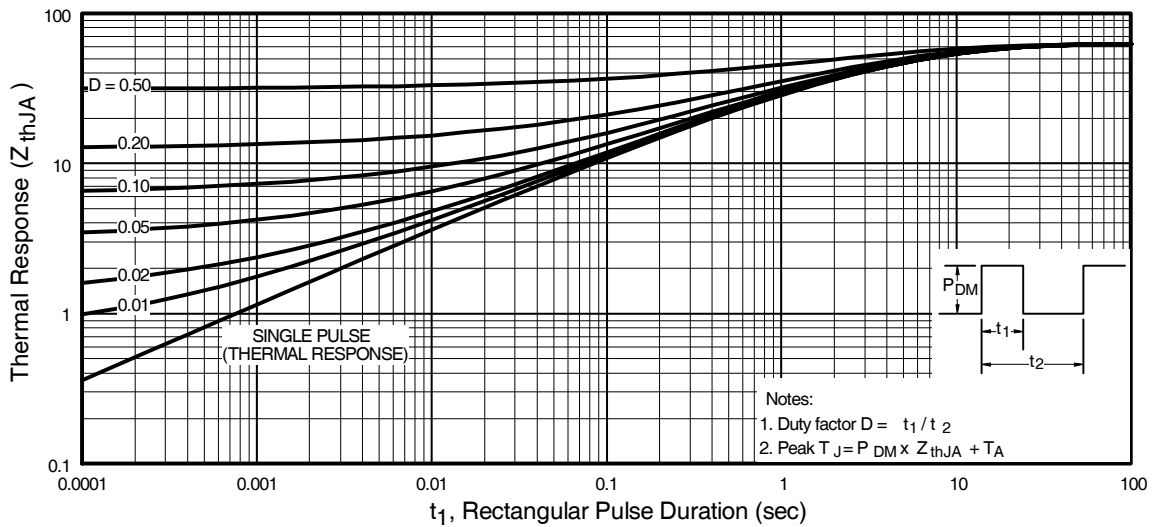


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

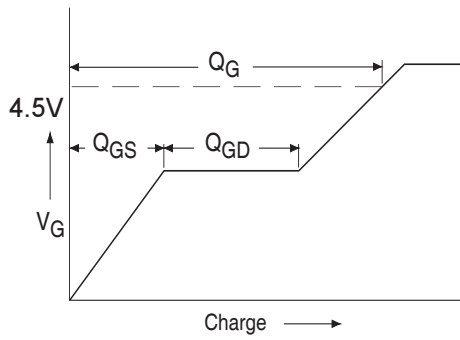


Fig 12a. Basic Gate Charge Waveform

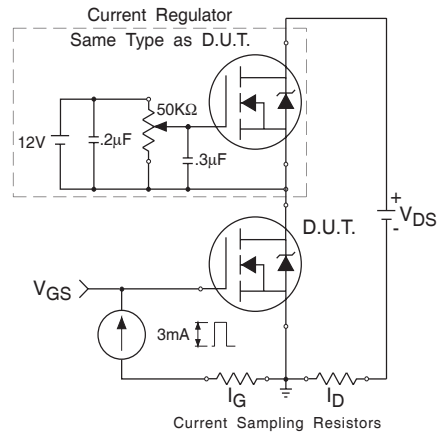
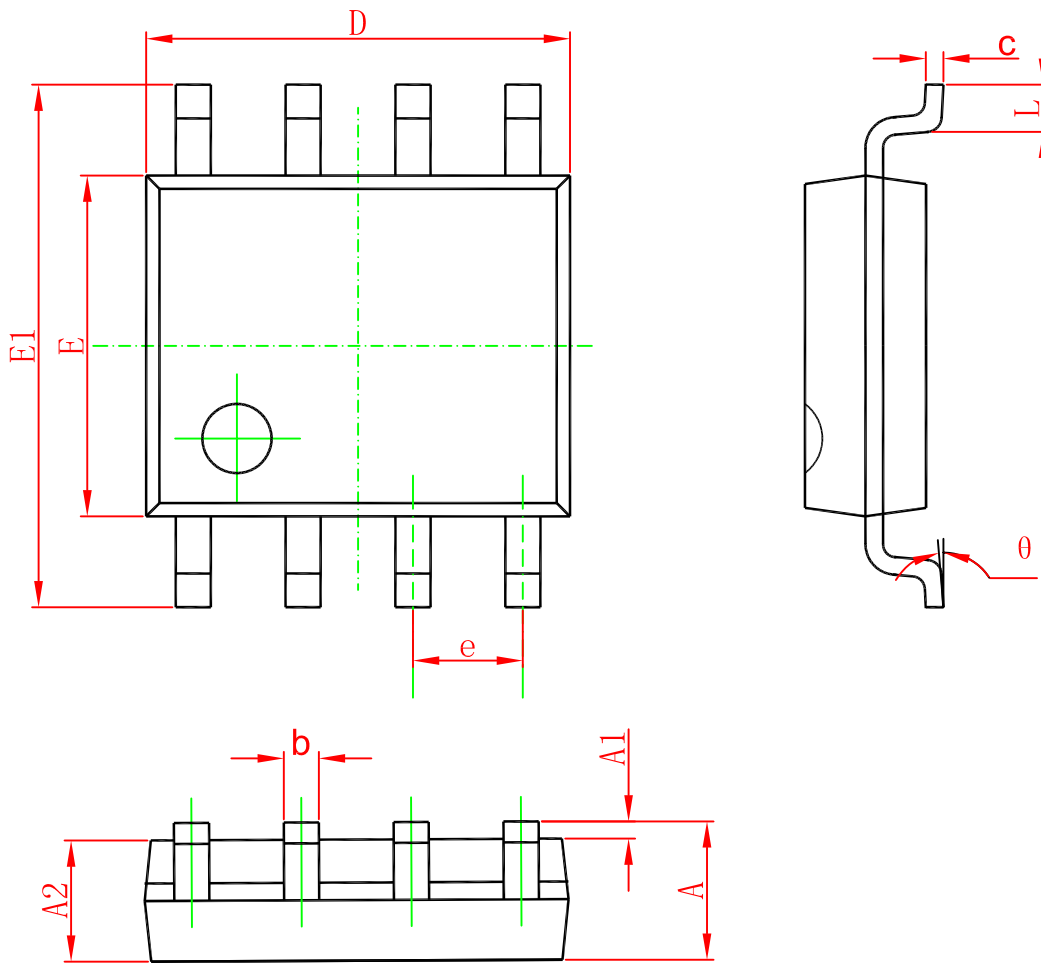


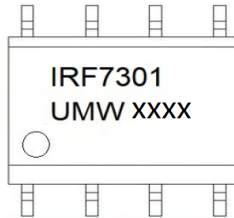
Fig 12b. Gate Charge Test Circuit

SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW IRF7301TR	SOP-8	3000	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)